Daniel Jacobsson Madsen

List of Publications by Year
in descending order

43 papers	1,472 citations	304743 22 h-index	315739 38 g-index
44 all docs	44 docs citations	44 times ranked	1719 citing authors

#	Article	IF	Citations
1	Direct Observations of Twin Formation Dynamics in Binary Semiconductors. ACS Nanoscience Au, 2022, 2, 49-56.	4.8	8
2	Post-nucleation evolution of the liquidâ€“solid interface in nanowire growth. Nanotechnology, 2022, 33, 105607.	2.6	3
3	Directed Selfâ€Assembly for Dense Vertical IIIâ€“V Nanowires on Si and Implications for Gate Allâ€Around Deposition. Advanced Electronic Materials, 2022, 8, .	5.1	1
4	Interface Dynamics in Agâ€“Cu₃P Nanoparticle Heterostructures. Journal of the American Chemical Society, 2022, 144, 248-258.	13.7	10
5	Enabling <i>In Situ</i> Studies of Metal-Organic Chemical Vapor Deposition in a Transmission Electron Microscope. Microscopy and Microanalysis, 2022, 28, 1484-1492.	0.4	11
6	Vaporâ€“solidâ€“solid growth dynamics in GaAs nanowires. Nanoscale Advances, 2021, 3, 5928-5940.	4.6	16
7	Time-resolved compositional mapping during in situ TEM studies. Ultramicroscopy, 2021, 222, 113193.	1.9	4
8	Compositional Correlation between the Nanoparticle and the Growing Au-Assisted In_{<i>x</i>}Ga_{1â€“<i>x</i>}As Nanowire. Journal of Physical Chemistry Letters, 2021, 12, 7590-7595.	4.6	12
9	Measuring Surface Tension of III-V Nanowire Au-Catalyst Droplets with an E-field. Microscopy and Microanalysis, 2021, 27, 27-28.	0.4	0
10	Limits of IIIâ€“V Nanowire Growth Based on Droplet Dynamics. Journal of Physical Chemistry Letters, 2020, 11, 2949-2954.	4.6	14
11	In situ metal-organic chemical vapour deposition growth of IIIâ€“V semiconductor nanowires in the Lund environmental transmission electron microscope. Semiconductor Science and Technology, 2020, 35, 034004.	2.0	20
12	Independent Control of Nucleation and Layer Growth in Nanowires. ACS Nano, 2020, 14, 3868-3875.	14.6	31
13	Evaluation of carrier density and mobility in Mn ion-implanted GaAs:Zn nanowires by Raman spectroscopy. Nanotechnology, 2020, 31, 205705.	2.6	2
14	In situ analysis of catalyst composition during gold catalyzed GaAs nanowire growth. Nature Communications, 2019, 10, 4577.	12.8	49
15	Raman characterization of single-crystalline Ga0.96Mn0.04As:Zn nanowires realized by ion-implantation. Nanotechnology, 2019, 30, 335202.	2.6	3
16	Kinetics of Auâ€“Ga Droplet Mediated Decomposition of GaAs Nanowires. Nano Letters, 2019, 19, 3498-3504.	9.1	18
17	Real-time, in situ, atomic scale observation of soot oxidation. Carbon, 2019, 145, 149-160.	10.3	49
18	Bending and Twisting Lattice Tilt in Strained Coreâ€“Shell Nanowires Revealed by Nanofocused X-ray Diffraction. Nano Letters, 2017, 17, 4143-4150.	9.1	43

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19	Real-time in-situ Investigation of III-V Nanowire Growth using Custom-designed Hybrid Chemical Vapor Deposition-TEM. Microscopy and Microanalysis, 2017, 23, 1716-1717.	0.4	1
20	Sn-seeded GaAs nanowires grown by MOVPE. Nanotechnology, 2016, 27, 215603.	2.6	7
21	Strategies to obtain pattern fidelity in nanowire growth from large-area surfaces patterned using nanoimprint lithography. Nano Research, 2016, 9, 2852-2861.	10.4	56
22	Interface dynamics and crystal phase switching in GaAs nanowires. Nature, 2016, 531, 317-322.	27.8	272
23	Low Trap Density in InAs/High-<i>k</i> Nanowire Gate Stacks with Optimized Growth and Doping Conditions. Nano Letters, 2016, 16, 2418-2425.	9.1	31
24	Phase Transformation in Radially Merged Wurtzite GaAs Nanowires. Crystal Growth and Design, 2015, 15, 4795-4803.	3.0	27
25	Sn-Seeded GaAs Nanowires as Self-Assembled Radial <i>pâ€“n</i> Junctions. Nano Letters, 2015, 15, 3757-3762.	9.1	25
26	Confinement in Thickness-Controlled GaAs Polytype Nanodots. Nano Letters, 2015, 15, 2652-2656.	9.1	62
27	Crystal phase control in GaAs nanowires: opposing trends in the Ga- and As-limited growth regimes. Nanotechnology, 2015, 26, 301001.	2.6	43
28	IIIâ€“V Nanowire Complementary Metalâ€“Oxide Semiconductor Transistors Monolithically Integrated on Si. Nano Letters, 2015, 15, 7898-7904.	9.1	71
29	Magnetoresistance in Mn ion-implanted GaAs:Zn nanowires. Applied Physics Letters, 2014, 104, 153112.	3.3	8
30	Observation of type-II recombination in single wurtzite/zinc-blende GaAs heterojunction nanowires. Physical Review B, 2014, 89, .	3.2	60
31	Enhanced sputtering and incorporation of Mn in implanted GaAs and ZnO nanowires. Journal Physics D: Applied Physics, 2014, 47, 394003.	2.8	24
32	FIB Plan and Side View Cross-Sectional TEM Sample Preparation of Nanostructures. Microscopy and Microanalysis, 2014, 20, 133-140.	0.4	23
33	Crystal structure tuning in GaAs nanowires using HCl. Nanoscale, 2014, 6, 8257.	5.6	9
34	GaAs/AlGaAs heterostructure nanowires studied by cathodoluminescence. Nano Research, 2014, 7, 473-490.	10.4	34
35	A General Approach for Sharp Crystal Phase Switching in InAs, GaAs, InP, and GaP Nanowires Using Only Group V Flow. Nano Letters, 2013, 13, 4099-4105.	9.1	156
36	Direct Imaging of Atomic Scale Structure and Electronic Properties of GaAs Wurtzite and Zinc Blende Nanowire Surfaces. Nano Letters, 2013, 13, 4492-4498.	9.1	63

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37	Magnetic Polarons and Large Negative Magnetoresistance in GaAs Nanowires Implanted with Mn Ions. Nano Letters, 2013, 13, 5079-5084.	9.1	26
38	Structural investigation of GaInP nanowires using X-ray diffraction. Thin Solid Films, 2013, 543, 100-105.	1.8	15
39	Control of composition and morphology in InGaAs nanowires grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2013, 383, 158-165.	1.5	39
40	Zincblendeâ€toâ€wurtzite interface improvement by group III loading in Auâ€seeded GaAs nanowires. Physica Status Solidi - Rapid Research Letters, 2013, 7, 855-859.	2.4	13
41	Single GaInP nanowire p-i-n junctions near the direct to indirect bandgap crossover point. Applied Physics Letters, 2012, 100, 251103.	3.3	13
42	Particle-assisted Ga_{<i>x</i>}In_{1â^’<i>x</i>}P nanowire growth for designed bandgap structures. Nanotechnology, 2012, 23, 245601.	2.6	48
43	High crystal quality wurtzite-zinc blende heterostructures in metal-organic vapor phase epitaxy-grown GaAs nanowires. Nano Research, 2012, 5, 470-476.	10.4	51